

TSM2N7002 60V N-Channel MOSFET

SOT-23

Pin Definition:



- 1. Gate 2. Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (mA)
60	7.5 @ V _{GS} = 10V	300
	7.5 @ V _{GS} = 4.5V	200

Features

- Fast Switching Speed
- Low Input and Output Leakage

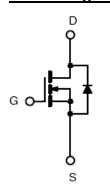
Application

- Direct Logic-Level Interface: TTL/CMOS
- Solid-State Relays

Ordering Information

Part No.	Package	Packing
TSM2N7002CX RF	SOT-23	3Kpcs / 7" Reel

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol Limit			Unit	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	300	mA	
Pulsed Drain Current		I _{DM}	800	mA	
Continuous Source Current (Diode Conduc	tion) ^{a,b}	Is	300	mA	
Maviroum Dawar Dissipation	Ta = 25°C	Б	350	mW	
Maximum Power Dissipation	Ta = 75°C	$ P_D$	220		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T _L	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ _{JA}	357	°C/W

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.

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60V N-Channel MOSFET

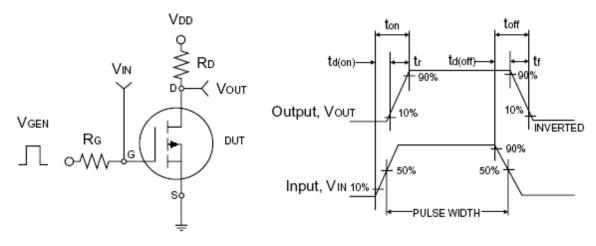
Pb Rohs COMPLIANCE

Electrical Specifications (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	Static					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu A$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.0		2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1.0	μA
Drain Course On State Desistance	$V_{GS} = 10V, I_D = 300mA$	Б			7.5	Ω
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 200mA$	$R_{DS(ON)}$			7.5	
Forward Transconductance	$V_{DS} = 15V, I_{D} = 300 \text{mA}$	g _{fs}		320		mS
Diode Forward Voltage	$I_S = 300 \text{mA}, V_{GS} = 0 \text{V}$	V_{SD}		0.9	1.2	V
Dynamic ^b						
Total Gate Charge	\/ - 10\/ - 250mA	Q_g		0.4	0.6	
Gate-Source Charge	$V_{DS} = 10V, I_D = 250mA,$ $V_{GS} = 4.5V$	Q_gs		0.06		nC
Gate-Drain Charge	V _{GS} - 4.5 V	Q_{gd}		0.06		
Input Capacitance	\/ - 25\/ \/ - 0\/	C _{iss}		50		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		25		pF
Reverse Transfer Capacitance	7 I = 1.0IVIDZ	C _{rss}		5		
Switching ^c						
Turn-On Delay Time		t _{d(on)}		7.5	20	
Turn-On Rise Time	$V_{DD} = 30V$,	t _r		6		nS
Turn-Off Delay Time	$I_D = 100 \text{mA}, V_{GEN} = 10 \text{V},$	t _{d(off)}		7.5	20] 113
Turn-Off Fall Time	$R_G = 10\Omega$	t _f		3		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

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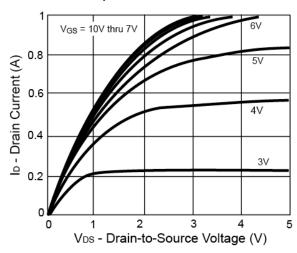


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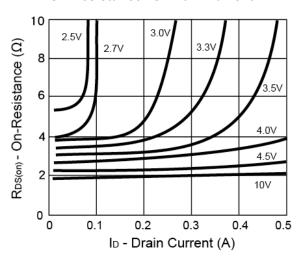


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

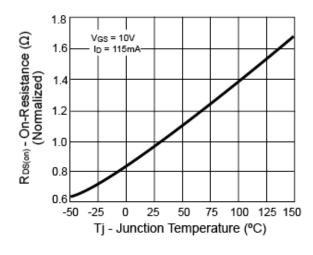
Output Characteristics



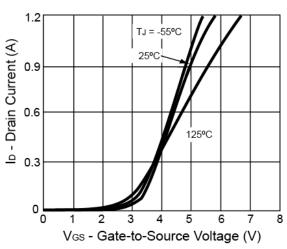
On-Resistance vs. Drain Current



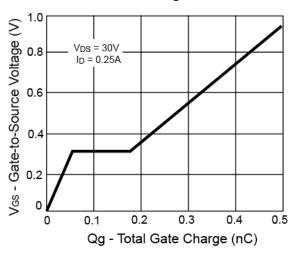
On-Resistance vs. Junction Temperature



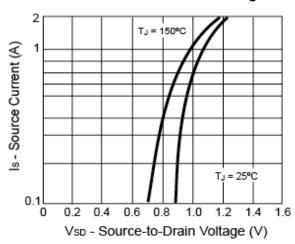
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



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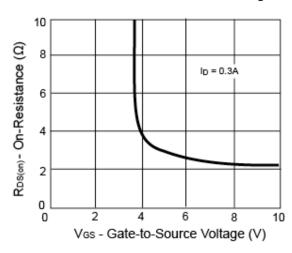


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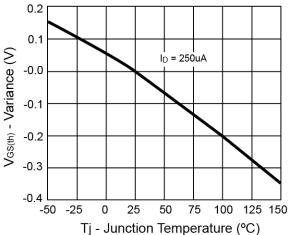


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

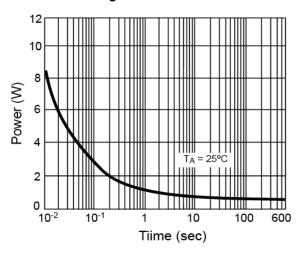
On-Resistance vs. Gate-Source Voltage



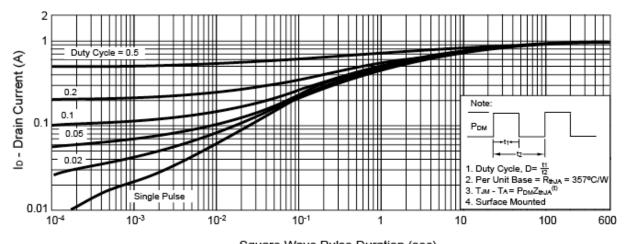
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

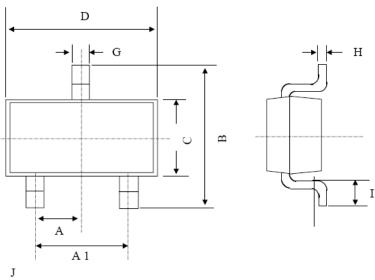
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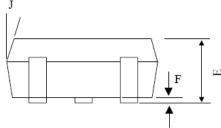
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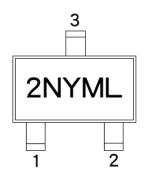
SOT-23 Mechanical Drawing



SOT-23 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95 BSC		0.037	BSC	
A1	1.9 I	BSC	0.074	BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



Marking Diagram



2N = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code

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